

SCIENTIFIC REPORTS



Corrigendum: Electron-hole transport and photovoltaic effect in gated MoS₂ Schottky junctions

Marcio Fontana, Tristan Deppe, Anthony K. Boyd, Mohamed Rinzan, Amy Y. Liu, Makarand Paranjape & Paola Barbara

Scientific Reports 3:1634; doi: 10.1038/srep01634; published online 09 April 2013; updated 30 July 2015

The authors made an error in the Discussion section of this paper.

“We estimate that the maximum electrical power that can be extracted from the device is about 2.5% of the laser power incident on the MoS₂ region between the electrodes.”

should read:

“We estimate that the maximum electrical power that can be extracted from the device is about 1.25% of the laser power incident on the MoS₂ region between the electrodes.”